

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: JAMES D. PARSONS

Title: ACOUSTIC ABSORPTION RADIATION SENSING IN SiC

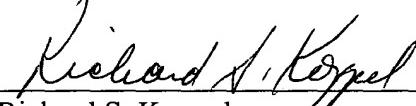
Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

TRANSMITTAL FOR INFORMATION DISCLOSURE STATEMENT

Sir:

Enclosed is an Information Disclosure Statement for the above application. We authorize the Commissioner to charge payment of any additional fees required in connection with this application to Deposit Account No. 11-1580. We enclose a copy of this sheet.

Respectfully submitted,


Richard S. Koppel
Richard S. Koppel
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Attorney for Applicant

September 5, 2003

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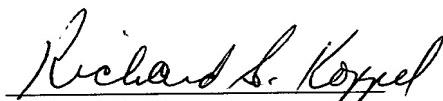
Sir:

Enclosed are Form PTO-1449 and copies of the listed non-U.S. patent references for the above application.

The filing of this information disclosure statement shall not be construed as a representation that a search has been made (37 C.F.R. 1.97(g)), an admission that the information cited is, or is considered to be, material to patentability, or that no other material information exists.

The filing of this information disclosure statement shall not be construed as an admission against interest in any manner. Notice of January 9, 1992, 1135 O.G. 13-25, at 25.

Respectfully submitted,



Richard S. Koppel
Registration No. 26,475
Attorney for Applicant

September 5, 2003

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FORM PTO-1449 (Modified) INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)	Docket No. 378-21-034 Applicant James D. Parsons	Application Number Group Art Unit
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U. S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	1.	DE VASCONCELOS E A ET AL: " <u>Highly sensitive thermistors based on high-purity polycrystalline cubic silicon carbide</u> " SENSORS AND ACTUATORS A, ELSEVIER SEQUOIA S.A., LAUSANNE, CH, Vol. 83, no. 1-3, May 2000 (2000-05), pages 167-171, XP004198310 ISSN: 0924-4247
	2	DE VASCONCELOS E A ET AL: " <u>Potential of high-purity polycrystalline silicon carbide for thermistor applications</u> " JAPANESE JOURNAL OF APPLIED PHYSICS, PART 1 (REGULAR PAPERS, SHORT NOTES & REVIEW PAPERS), SEPT. 1998, PUBLICATION OFFICE, JAPANESE JOURNAL APPL. PHYS, JAPAN, vol. 37, no. 9A, pages 5078-5079, XP002211060 ISSN: 0021-4922
	3	<u>Materials for High Temperature Semiconductor Devices</u> : Committee on Materials for High-Temperature Semiconductor Devices, National Materials Advisory Board, Commission on Engineering and Technical Systems, National Research Council: National Academy Press, Washington, D.C., 1995, pp.68-70.
	4	O. Nennewitz, L. Spiess and V. Breternitz, " <u>Ohmic Contacts to 6H-SiC</u> ", Applied Surface Science, Vol. 91, 1995, pages 347-351.
	5	J.A. Lely and F.A. Kroeger, " <u>Electrical Properties of Hexagonal SiC Doped with N, B or Al</u> ", In Semiconductors and Phosphors, Proceedings of Int'l. Colloquium-Partenkirchen, Ed. M. Schoen and H. Welker, New York, Interscience Pub., Inc. 1958, pp. 525-533.
	6	Q.Y. Tong, U. Gosele, C. Yuan, A.J. Stecki & M. Reiche, " <u>Silicon Carbide Wafer Bonding</u> ", J. Electrochem Soc., Vol. 142, No. 1, January 1995, pp. 232-236.

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	7	Choyke,W.J., "Optical and Electronic Properties of SiC" NATO ASI Series Vol. "The Physics and Chemistry of Carbides, Nitrides and Borides", Manchester, England, pp. 1-25, 9/18-22,1999
	8	Spitzer et al., "Infrared Properties of Hexagonal Silicon Carbide", Physical Review, Vo. 113, No. 1, pp. 127-132, January 1, 1959.
	9	Electronic Properties Information Center, "Silicon Carbide", Hughes Aircraft Company, June 1965, pp. 9-16.
	10	P.K. Bhattacharya, "Bonding of SiC Slabs for Electro-Mechanical Heat-Sinks in Advanced Packaging Applications", J. Electronics, Vol. 73, No. 1, 1992, pp. 71-83.
	11	Westinghouse Astronuclear Laboratory "Silicon Carbide Junction Thermistor", 1965
	12	Jeffrey B. Casady et al, "A Hybrid 6H-Sic temperature Sensor Operational from 25°C to 500°C, IEEE Transactions on Components, Packaging and Manufacturing Technology" - Part A, Vol. 19, No. 3 (September 1996, pp 416-422.

Examiner	Date Considered
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		Takashi Nagel and Masahiko Itch, "Sic Thin-Film Thermistors", IEEE Transactions on Industry Applications, Vol. 26, No. 6, November/December 1990, pp. 1139-1143.1
13		"Electrical Properties of β -Sic Heavily Doped with Nitrogen" O. A. Golikova, L.M. Ivanova, A. A. Pletyushin, and V.P. Semenenko, A.A. Balkov Institute of Metallurgy, Academy of Sciences of the USSR, Moscow Institute of Semiconductors, Academy of Sciences of the USSR, Leningrad Translated from Fizika I Tehnika Poluprovodnikov, Vol. 5, No. 3, pp. 417-420, March 1971, Original article submitted May 26, 1970; revision submitted July 8, 1970.
14		"Galvanomagnetic Effects in n-type Silicon Carbide at Low Temperatures", M.I. Iglitsyn, M. Mirzabaev, V.M. Tuchkevich, E.F. Fedorova, and Yu. V. Shmartsev, A.F. Ioffe Physicotechnical Institute, Academy of Sciences, USSR, Leningrad State Research and Planning Institute for the Rare Metal Industry, Moscow, Translated from fizika Tverdogo Tela, Vol. 6, No. 9, pp. 2673-2682, September, 1964, Originak article submitted March 31, 1964
15		
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